Docket No.: 57810-031 **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2815

Examiner:

In re Application of

· Tatsuya KUNISATO, et al.

Serial No.: 10/081,842

Filed: February 25, 2002

1 110d. 1 001ddi y 23, 2002

For: NITRIDE-BASED SEMICONDUCTOR ELEMENT AND METHOD OF FORMING

NITRIDE-BASED SEMICONDUCTOR

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS

Commissioner for Patents Washington, DC 20231

Sir:

We are in receipt of the Notice to File Corrected Application Papers mailed March 19, 2002.

In response to this Notice, submitted herewith is an Abstract not exceeding 150 words (37 CFR 1.72 (b)). If anything further is needed, please contact the undersigned immediately.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Date: May 17, 2002